

# Analog Section for the Silicon Strip Detectors of the Super B SVT Inner Layers

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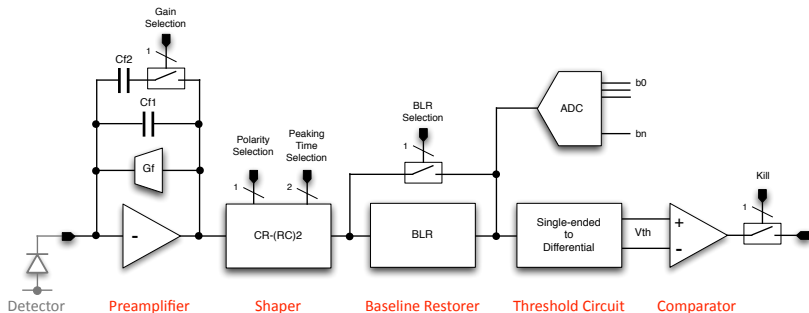
**2<sup>nd</sup> SuperB Collaboration Meeting @ INFN-LNF**

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# Electronic Readout for SVT Inner Layers (L0-L3)

- **Microstrips and striplets detectors** are the baseline option for the design of the SVT fast (Layers 0 to 3) front-end at SuperB
- **ASIC**: the signals from the silicon strip detectors will be processed by a custom-designed IC based on a 130 nm planar technology with 128 channels
- **Analog Channel**
  - amplification
  - filtering
  - threshold discrimination
  - 3-4 bit analog information about the signal amplitude
- **Main requirements**
  - **Operating temperature**:  $<40$  °C
  - **Radiation tolerance**:  $>3$  Mrad/year for 10 years
  - **Power dissipation**:  $<4$  mW/channel
  - **Signal polarity**: readout channel should be capable of reading signals from both P and N-side of the strip detectors
  - **Dynamic range**: 10-15 MIP charge
  - **Analog Resolution**: 0.2 MIP minimum input charge
  - **Hit efficiency**:  $>95\%$  at design luminosity
  - **Peaking Time**:  $\leq 25$  ns for Layer 0
  - **Signal-to-Noise Ratio**:  $>20$
  - **Threshold dispersion**:  $<300$  e- rms
- **Simulation results for a preliminary version of the charge preamplifier and the shaping stage of the SVT inner layers will be shown**

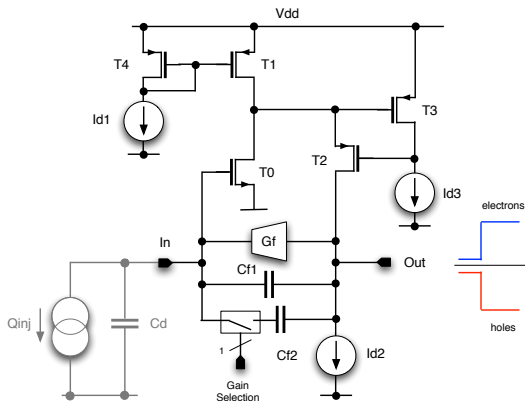
# Analog channel block diagram



The analog channel consists of

- **Charge-sensitive preamplifier** with gain selection (1 bit)
- **Unipolar semi-Gaussian shaper** with polarity (1 bit) and peaking time (2 bit) selection options
- **Symmetric baseline restorer** to achieve baseline shift suppression, may be included or not (1 bit)
- **Hit discriminator** threshold circuit and comparator
- **3-4 bit analog-to-digital conversion** will be performed by a Flash ADC or by means of a Time-Over-Threshold (TOT) detection

# Charge Sensitive Amplifier

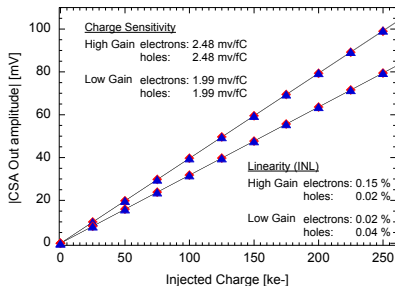
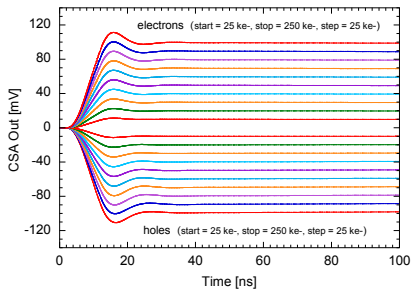


## Main design features

Chip Bias	1.2 V
$V_{DD}$	
PA input $W/L$	2000/0.2
PA input $I_D$	500 $\mu$ A
Power consumption	1.1 mW
Feedback	400 fF
$C_{f1}, C_{f2}$	100 fF
Reset	100 nS
$G_f$	

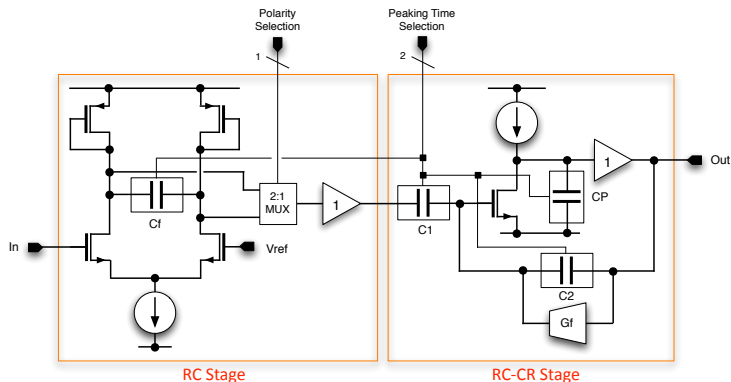
- **Architecture:** active folded cascode (with local feedback) loaded by an active cascoded load
- **Sensitivity:** low gain 2.0 mV/fC ( $C_f = C_{f1} + C_{f2}$ ), high gain 2.5 mV/fC ( $C_f = C_{f1}$ )
- **Reset:** performed by a time continuous feedback network implemented with a differential pair ( $\tau \approx 5 \mu$ s at low gain and  $\approx 4 \mu$ s at high gain)

# CSA response and dynamic range



- **Rise time:**  $t_r=7$  ns for both holes and electrons
- **Charge sensitivity:** low gain 1.99 mV/fC (electrons and holes), high gain 2.48 mV/fC (electrons and holes)
- **Dynamic range:** the CSA covers the full dynamic range of 15 MIP (240 ke- in L0) for both the input signal polarities and gain settings
- **Linearity:** <0.2 %

# Shaping circuit



- **Shaping function:** Unipolar semi-Gaussian ( $RC^2$ -CR)
- **Polarity selection** (1 bit): allows to operate with signals delivered both from n- and p- sides of double-sided strip detectors
- **Peaking time selection** (2 bit): obtained by setting the values of capacitances in the shaper according to the following relationships (with  $t_{P0}=25$  ns,  $C_0=50$  fF and  $n=1,2,4,8$ ):

$$t_P = n \cdot t_{P0}$$

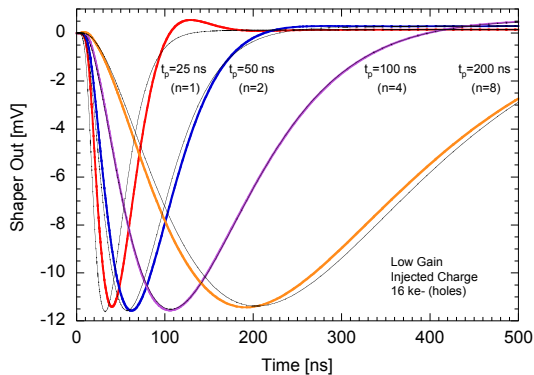
$$C_P = n \cdot C_0$$

$$C_1 = n \cdot 4 \cdot C_0$$

$$C_2 = n \cdot 2 \cdot C_0$$

$$C_f = n \cdot 2.5 \cdot C_0$$

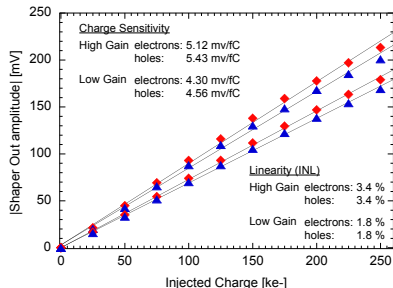
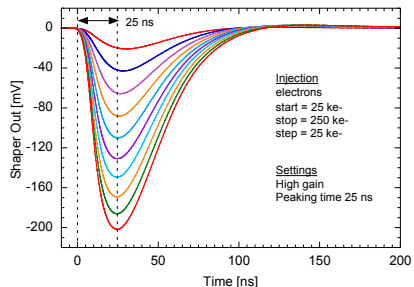
# Peaking Time Selection



$n$	Peaking Time [ns]	
	Nominal	Simulated
1	25	30
2	50	55
4	100	100
8	200	190

- Good agreement between ideal (black lines) and simulated (colored lines) shaping functions and peaking times
- A better matching can be obtained with a fine tuning of the shaping circuit capacitances (to be done)

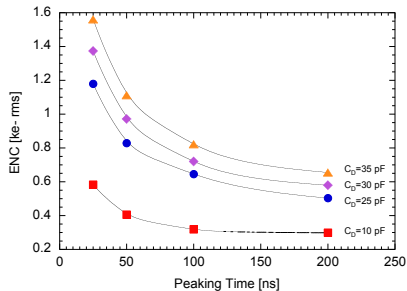
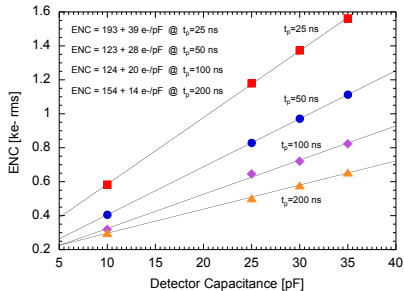
# Shaper Output response and dynamic range



- **Charge sensitivity:** low gain  $\approx 4.5$  mV/fC (electrons and holes), high gain  $\approx 5.5$  mV/fC (electrons and holes)
- **Dynamic range:** the shaper covers the full dynamic range of 15 MIP (240 ke- in L0) for both the input signal polarities and gain settings
- **Linearity:** worst in high gain setting ( $\approx 3.5$  %) with respect to low gain setting ( $\approx 2$  %)



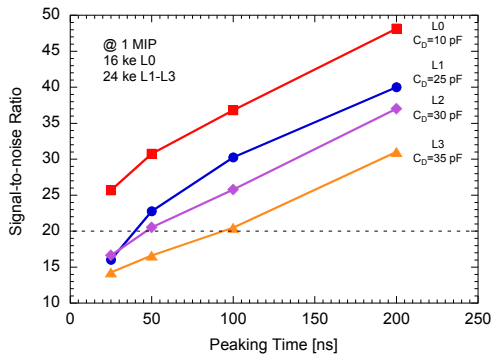
# Equivalent Noise Charge



Layer	$C_D$ [pF]	$t_p$ [ns]	ENC	ENC	S/N (1 MIP)
			$R_S$ [e rms]	CSA [e rms]	
0	10	25	220	580	26
1	25	100	460	650	30
2	30	100	590	720	26
3	35	200	410	660	31

S/N >20 for all the layers (1 MIP is 16 ke- in L0 and 24 ke- in L1 to L3)

# S/N ratio vs $t_p$ at 1 MIP



- **L1 and L2:** S/N remains  $>20$  moving from the foreseen peaking time of 100 ns to 50 ns
- **L3:** S/N remains  $>20$  moving from 200 ns to 100 ns

- Simulation of the charge preamplifier and the shaping stage of the SVT inner layers almost complete
- Power consumption  $< 4$  mW/channel
- Charge sensitivity: adjust the low gain to best fit the 2/3 ratio as for the charge delivered by sensors belonging to different layers
- Threshold adjustment at strip level could be necessary due to the low value of charge sensitivity
- Good performance in terms of noise ( $S/N > 20$  for all layers)
- In next weeks the design of the remaining blocks (BLR and threshold discriminator) will be also completed in order to have a preliminary version of the channel ready for the TDR

# Backup Slides

# Microstrip detector: proposed layer grouping

Layer	$C_D$ [pF]	available $t_p$ [ns]	selected $t_p$ [ns]	ENC from $R_S$ [e rms]	ENC [e rms]	Channel width [ $\mu\text{m}$ ]	Hit rate/strip [kHz]	Efficiency $1/(1+N)$
0	11.2	25, 50, 100, 200	25	220	<b>740</b>	3000	2060	0.890
1	26.7		100	460	<b>940</b>		697	0.857
2	31.2		100	590	<b>1100</b>		422	0.908
3	34.4		200	410	<b>940</b>		325	0.865
4	52.6	400, 600, 800, 1000 (or 500 and 1000)	500	490	<b>1000</b>	9000	47	<b>0.947</b>
			600	440	<b>940</b>			0.937
5	67.5		800	560	<b>1090</b>		28	0.949
			1000	500	<b>1030</b>			<b>0.937</b>